



DMTH6004SK3Q

Product Summary

BV _{DSS}	R _{DS(ON)} Max	Q _G Тур	I _D Max T _C = +25°C (Note 10)
60V	3.8mΩ @ V _{GS} = 10V	95.4nC	100A

60V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} Minimizes Power Losses
- Low Q_G Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)

UL Flammability Classification Rating 94V-0

Moisture Sensitivity: Level 1 per J-STD-020

Solderable per MIL-STD-202, Method 208 @3

Weight: 0.33 grams (Approximate)

- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Case Material: Molded Plastic, "Green" Molding Compound.

Terminals: Finish - Matte Tin Annealed over Copper Leadframe.

• PPAP Capable (Note 4)

Case: TO252 (DPAK)

Mechanical Data

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Description and Applications

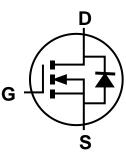
This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

TO252 (DPAK)

Top View

- Engine Management Systems
- Body Control Electronics
- DC-DC Converters
- Motor Control

Top View Pin Out



Internal Schematic

Ordering Information (Note 5)

Part Number	Case	Packaging
DMTH6004SK3Q-13	TO252 (DPAK)	2,500/Tape & Reel

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Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

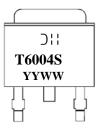
 See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



D11=Manufacturer's Marking T6004S = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 16 = 2016) WW = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	60	V	
Gate-Source Voltage	V _{GSS}	±20	V	
Continuous Drain Current (Note 7)	T _C = +25°C (Note 10)	ID	100	A
	T _C = +100°C	_	75	
Maximum Body Diode Forward Current (Note 7)	ls	100	A	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	IDM	150	A	
Avalanche Current, L = 0.2mH	I _{AS}	45	A	
Avalanche Energy, L = 0.2mH	E _{AS}	200	mJ	

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	T _A = +25°C	PD	3.9	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	38	°C/W	
Total Power Dissipation (Note 7)	PD	180	W	
Thermal Resistance, Junction to Case (Note 7)	R _{θJC}	0.8	°C/W	
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +175	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	_		V	$V_{GS} = 0V, I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}			1	μΑ	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}		_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	2	—	4	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}		3	3.8	mΩ	$V_{GS} = 10V, I_D = 90A$	
Diode Forward Voltage	V _{SD}		0.9	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	CISS		4,556	—	pF	$V_{DS} = 30V, V_{GS} = 0V, f = 1MHz$	
Output Capacitance	Coss		1,383	—			
Reverse Transfer Capacitance	C _{RSS}		105.2				
Gate Resistance	R _G		0.66		Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge	Q_G		95.4	—		$V_{DS} = 30V, I_D = 90A, V_{GS} = 10V$	
Gate-Source Charge	Q _{GS}	_	21.6	_	nC		
Gate-Drain Charge	Q _{GD}	_	20.4	—			
Turn-On Delay Time	t _{D(ON)}	_	13.2	_		$V_{DD} = 30V, V_{GS} = 10V,$ $I_D = 90A, R_G = 3.5\Omega$	
Turn-On Rise Time	t _R	_	11.7	_	ns		
Turn-Off Delay Time	t _{D(OFF)}	_	31	_			
Turn-Off Fall Time	t _F	_	12	_	1		
Body Diode Reverse Recovery Time	t _{RR}	_	50.5	—	ns		
Body Diode Reverse Recovery Charge	Q _{RR}		80.8	_	nC	- I _F = 50A, di/dt = 100A/μs	

Notes: 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.

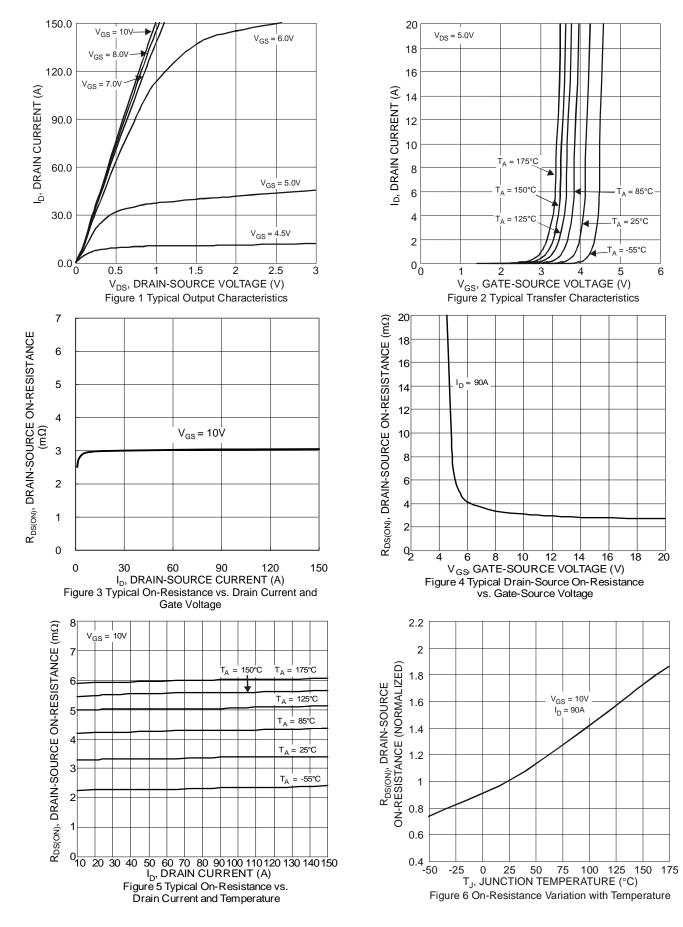
Thermal resistance from junction to soldering point (on the exposed drain pad).
Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to production testing.

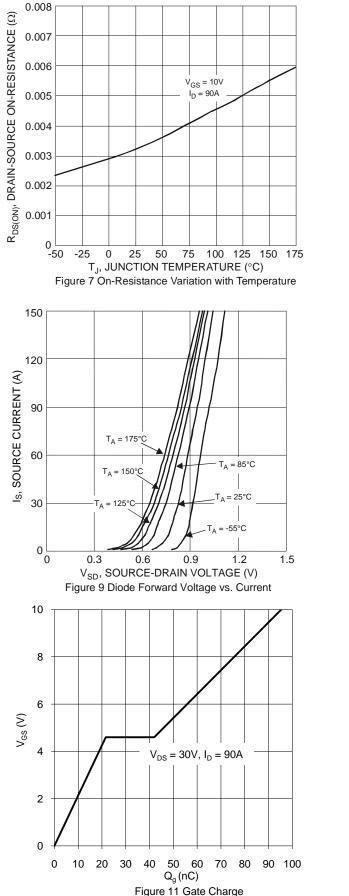
10. Package limited.

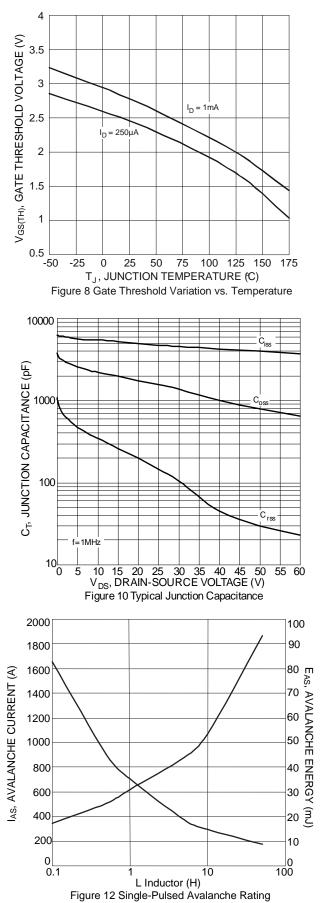


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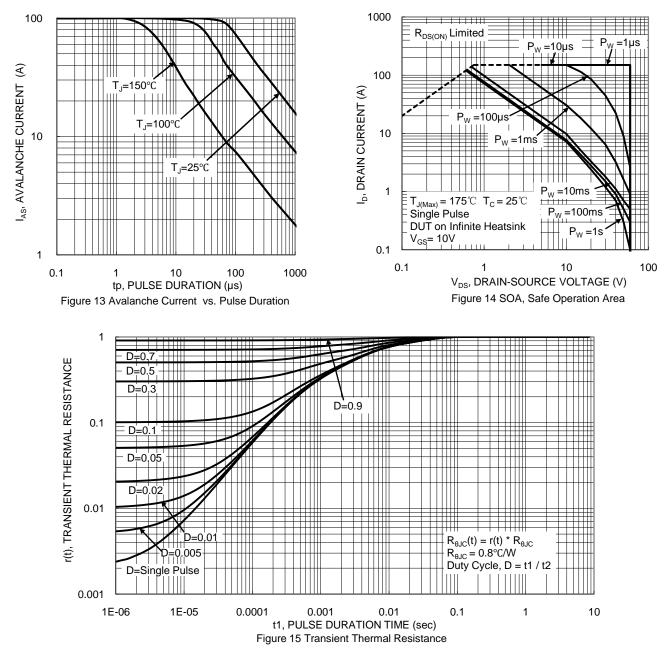




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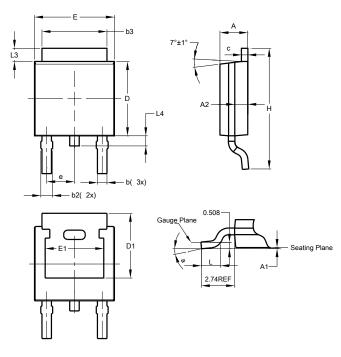




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)

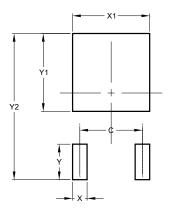


TO252 (DPAK)						
Dim	Min	Max	Тур			
Α	2.19	2.39	2.29			
A1	0.00	0.13	0.08			
A2	0.97	1.17	1.07			
b	0.64	0.88	0.783			
b2	0.76	1.14	0.95			
b3	5.21	5.46	5.33			
С	0.45	0.58	0.531			
D	6.00	6.20	6.10			
D1	5.21	-	-			
е	-	-	2.286			
Е	6.45	6.70	6.58			
E1	4.32	-	-			
Н	9.40	10.41	9.91			
L	1.40	1.78	1.59			
L3	0.88	1.27	1.08			
L4	0.64	1.02	0.83			
а	0°	10°	_			
All	All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)		
С	4.572		
Х	1.060		
X1	5.632		
Y	2.600		
Y1	5.700		
Y2	10.700		



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